

# COMPUTER DIODE

200mA

Low Power, Switching

1N3600; JAN, JANTX & JANTXV 1N3600  
 1N4150; JAN, JANTX & JANTXV 1N4150  
 JAN, JANTX & JANTXV 1N4150-1

## FEATURES

- Metallurgical Bond
- Qualified to MIL-S-19500/231
- Planar Passivated Chip
- DO-7 or DO-35 Package
- Non-JAN Available

## DESCRIPTION

This series of switching diodes is useful in many computer switching applications, for both military and commercial systems.

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## ABSOLUTE MAXIMUM RATINGS, AT 25°C

Reverse Breakdown Voltage .....	75V
Peak Working Voltage .....	50V
Average Output Current .....	200mA
Surge Current (1sec) .....	0.5A
(1 $\mu$ sec) .....	4.0A
Operating Temperature Range .....	-65°C to +175°C
Storage Temperature Range (1N4150) .....	-65°C to +200°C
(1N3600) .....	-65°C to +175°C

## MECHANICAL SPECIFICATIONS

**J, JTX & JTXV 1N3600**

	INCHES	MILLIMETERS
A	.078 - .107	1.98 - 2.72
B	.195 - .300	4.96 - 7.62
C	1.0 MIN. - 1.5 MAX.	25.4 MIN. - 38.1 MAX.
D	.018 - .022	.46 - .56

**J, JTX & JTXV 1N4150, 1N4150-1**

	INCHES	MILLIMETERS
A	.066 - .076	1.42 - 1.91
B	.140 - .180	3.56 - 4.57
C	1.0 MIN. - 1.5 MAX.	25.4 MIN. - 38.1 MAX.
D	.018 - .022	.46 - .56

**DO-7  
1N3600**

**DO-35  
1N4150**

**ELECTRICAL SPECIFICATIONS (at 25°C unless noted)**

Characteristics	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Reverse Breakdown Voltage
Conditions	$V_{F1}$ $I_F = 1 \text{ mAdc}$	$V_{F2}$ $I_F = 10 \text{ mAdc}$	$V_{F3}$ $I_F = 50 \text{ mAdc}$ (pulse)	$V_{F4}$ $I_F = 100 \text{ mAdc}$ (pulse)	$V_{F5}$ $I_F = 200 \text{ mAdc}$ (pulse)	BV $I_R = 5.0 \text{ } \mu\text{A}$
Minimum	0.540 Vdc	0.660 Vdc	0.760 Vdc	0.820 Vdc	0.870 Vdc	75 Vdc
Maximum	0.620 Vdc	0.740 Vdc	0.860 Vdc	0.920 Vdc	1.00 Vdc	—

  

Characteristics	Reverse Current	Reverse Current	Junction Capacitance	Reverse Recovery Time	Reverse Recovery Time	Forward Recovery Time
Conditions	$I_R$ $V_R = 50 \text{ Vdc}$	$I_R$ $V_R = 50 \text{ Vdc}$ $T_A = 150^\circ\text{C}$	C $V_R = 0$ F = 1 MHz $V_{sig} = 50 \text{ mv (p-p)}$	$t_{rr1}$ $I_F = I_R =$ 10 to 200 mA; $R_L = 100 \text{ ohms}$	$t_{rr2}$ $I_F = I_R =$ 200 to 400 mA; $R_L = 100 \text{ ohms}$	$t_{fr}$ $I_F = 200 \text{ mA}$ ; $t_p = 100 \text{ nsec}$ ; $t_r = 0.4 \text{ nsec}$
Maximum	0.1 $\mu\text{A}$	100 $\mu\text{A}$	2.5 pf	4 nsec	6 nsec	10 nsec

